Tool ID: 115
Tool Location: 103

Equipment Information Sheet

CMOS N+ Polysilicon - D3

Manager: Phil Infante 607-254-4926
Backup: Aaron Windsor 607-254-4831

Calls to staff phones will be automatically forwarded to their cell phones during accessible hours. At other times leave a message or send them an email.

SAFETY

- The furnaces are run at elevated temperatures of 400-1200°C and use flammable, toxic, and corrosive gases.

USAGE RESTRICTIONS

- No changing of gas flows or process parameters without staff approval
- 650 C max process temperature

SCHEDULING/SIGN-UP RESTRICTIONS

Minimum Tool Time: 90 minutes

- Reservation blocks greater than 8 hrs must be cleared by a MOS staff person prior to reserving the time

MATERIALS COMPATIBILITY CATEGORY

Tool Category 1:Restriced Silicon Based Materials Only

Allowed	Not Allowed
Silicon Based Materials only (Si, SiC, SiO_2 substrates)	No Evaporated, Sputtered, or Spin on Films
All Furnace grown or deposited films	No ALD films
PECVD Films	No Metal or Organic Films
	No Glass Substrates
	No III/V Compound Semiconductors
	No Deep Silicon Etched Samples (versaline, Unaxis)
	No Organic/Biology Molecules prepared-with or without Salt buffers

Additional Material Restrictions and Exceptions

- MOS CLEAN required prior to use
- Only use designated MOS holders, wands and tweezers

Last Updated: 03/20/2019